

[TS10F6]**Nanoelectronic and Quantum Devices 6**

Date & Time	July 5(Fri.), 2024 / 09:00–10:15
Place	Room 206A
Session Chair(s)	Yonghun Kim (KIMS)

TS10F6_I_1 *Invited 09:00–09:30

Uniform TMDC Film Deposited by PVD Method

Hitoshi Wakabayashi

(Tokyo Institute of Technology)

TS10F6_O_2 09:30–09:45

MoS₂ Active Array for the High-Resolution Monitoring of Cortical Neuron Activity

Duo Xu, Juyeong Hong, and Jong-Hyun Ahn

(Yonsei University)

TS10F6_O_3 09:45–10:00

Electrical Characterization of Flash Memory-Based Synaptic using Liganded CdSe Quantum Dots

Jae Min Kim, Tae Hwan Koo, So Yeon Jung, Hyeong Jin Chae, Ju Yeong Chae, and Moon Gyu Jang

(Hallym University)

TS10F6_O_4 10:00–10:15

Fabrication of Thin SOI-Based Neuromorphic Transistors with Mesh-Type Floating Gate

Soyeon Jung, Hyeongjin Chae, Jaemin Kim, Taehwan Koo, Juyeong Chae, and Moongyu Jang

(Hallym University)